

## Description

The HM100N02 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

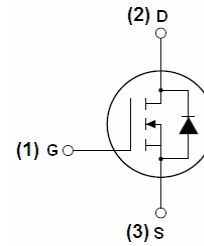
- $V_{DS} = 20V, I_D = 100A$   
 $R_{DS(ON)} < 5.5m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

## Application

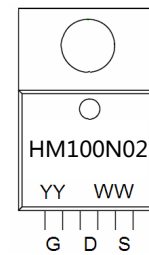
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

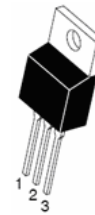
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin Assignment



TO-220 top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM100N02	HM100N02	TO-220-3L	-	-	-

## Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	100	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	70	A
Pulsed Drain Current	$I_{DM}$	350	A
Maximum Power Dissipation	$P_D$	60	W
Derating factor		0.48	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	2.1	$^\circ C/W$
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## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

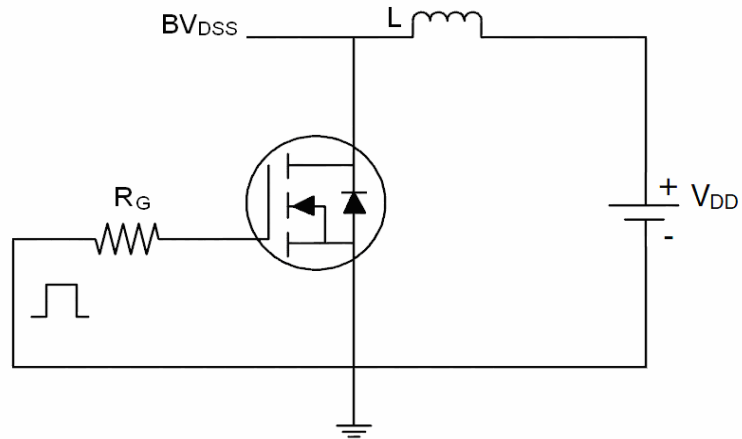
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.45	0.65	1.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40 A	-	4.5	5.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A		6.5	7.5	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =40A	15	-	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, F=1.0MHZ	-	2000	-	PF
Output Capacitance	C <sub>OSS</sub>		-	500	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	200	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =2A, R <sub>L</sub> =1Ω V <sub>GS</sub> =4.5V, R <sub>G</sub> =3Ω	-	6.4	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	17.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	29.6	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16.8	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =40A, V <sub>GS</sub> =10V	-	27		nC
Gate-Source Charge	Q <sub>gs</sub>		-	6.5		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6.4		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	100	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 40A di/dt = 100A/μs (Note3)	-	25	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	24	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

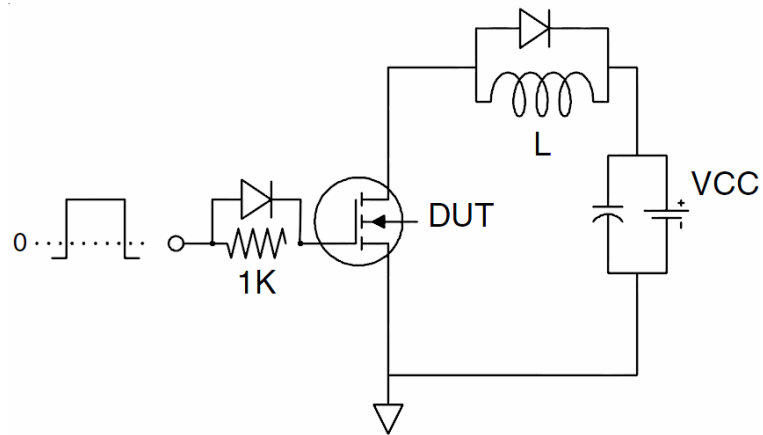
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E<sub>AS</sub> condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=10V, V<sub>G</sub>=10V, L=0.5mH, R<sub>g</sub>=25Ω.

## Test circuit

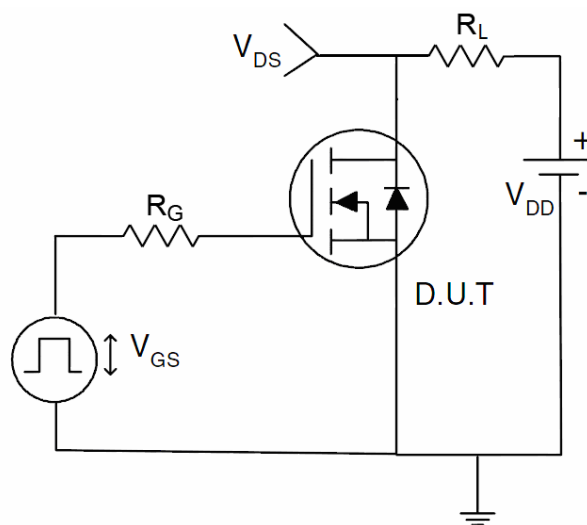
### 1) $E_{AS}$ Test Circuit



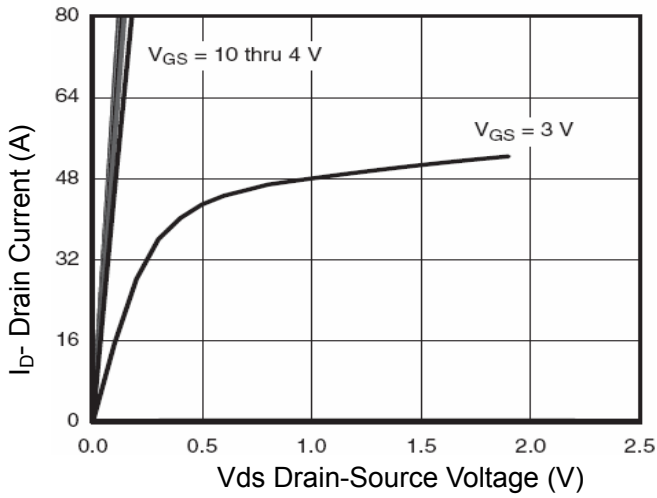
### 2) Gate Charge Test Circuit



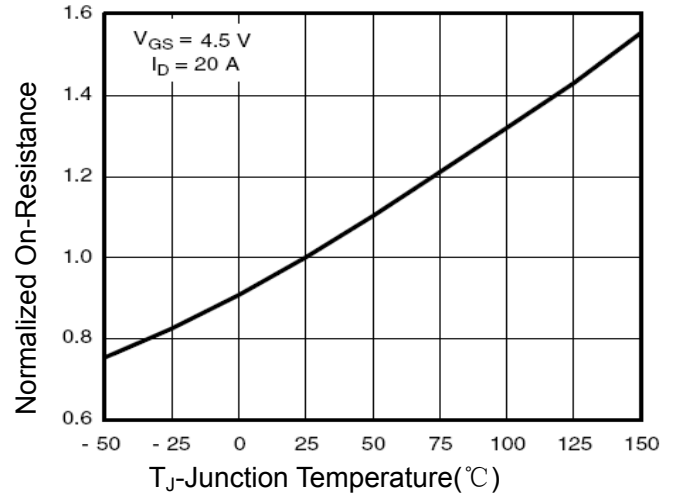
### 3) Switch Time Test Circuit



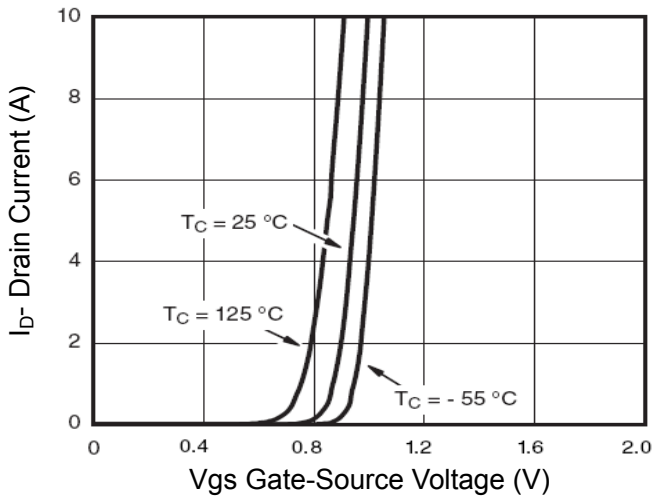
**Typical Electrical and Thermal Characteristics (Curves)**



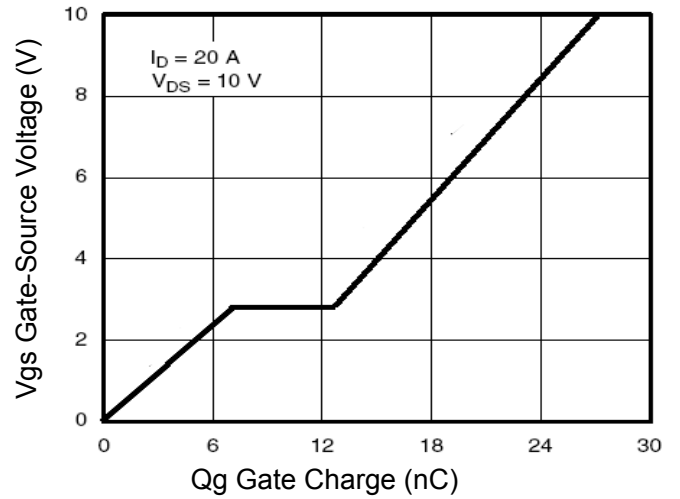
**Figure 1 Output Characteristics**



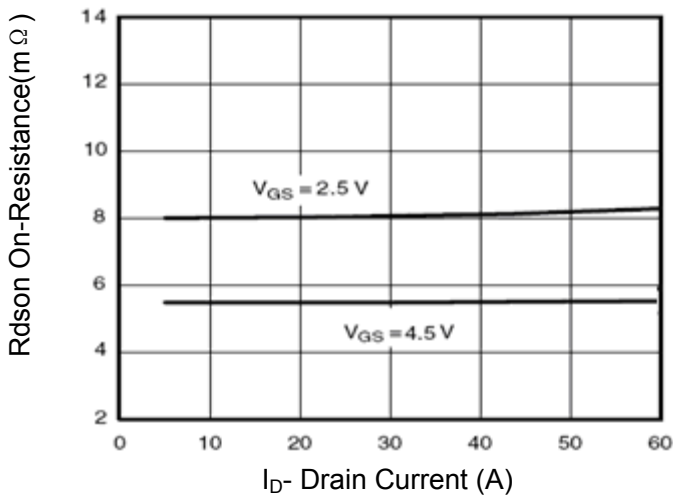
**Figure 4 Rdson-Junction Temperature**



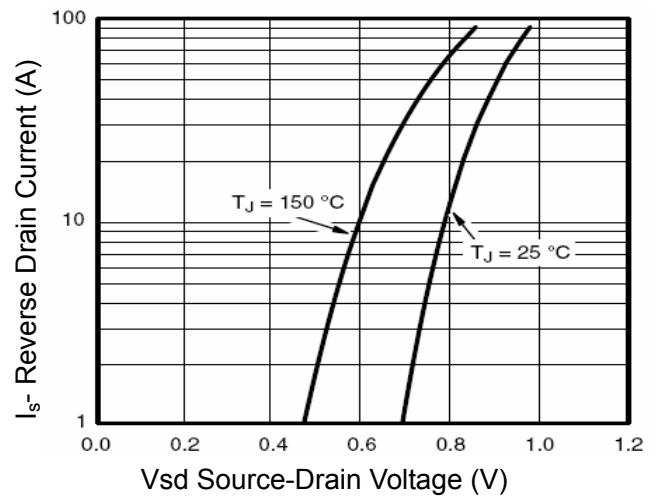
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drain Diode Forward**

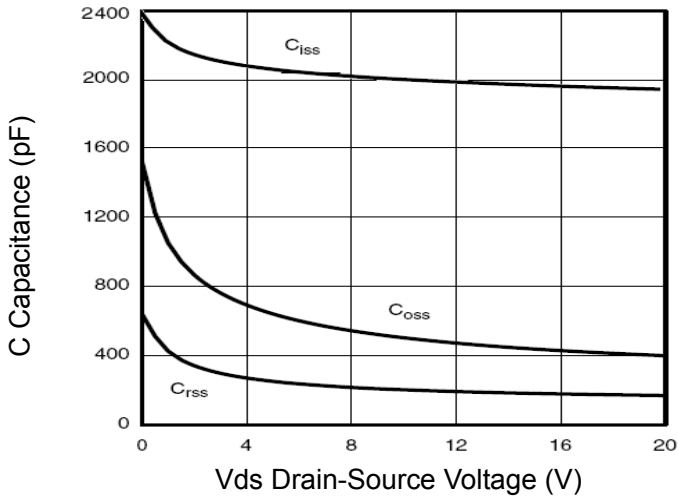


Figure 7 Capacitance vs Vds

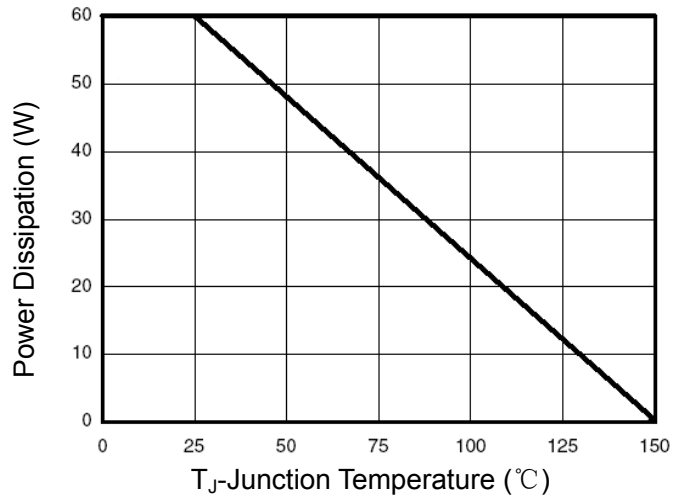


Figure 9 Power De-rating

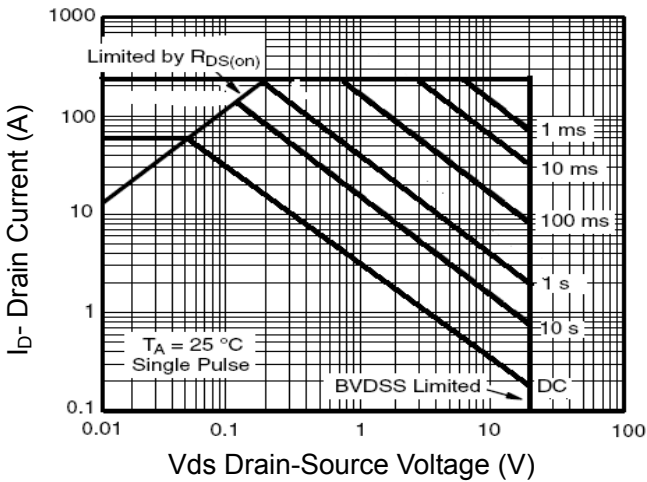


Figure 8 Safe Operation Area

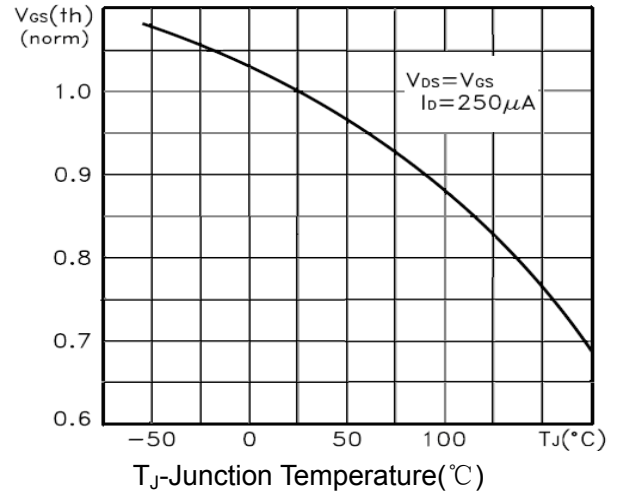


Figure 10  $V_{GS(th)}$  vs Junction Temperature

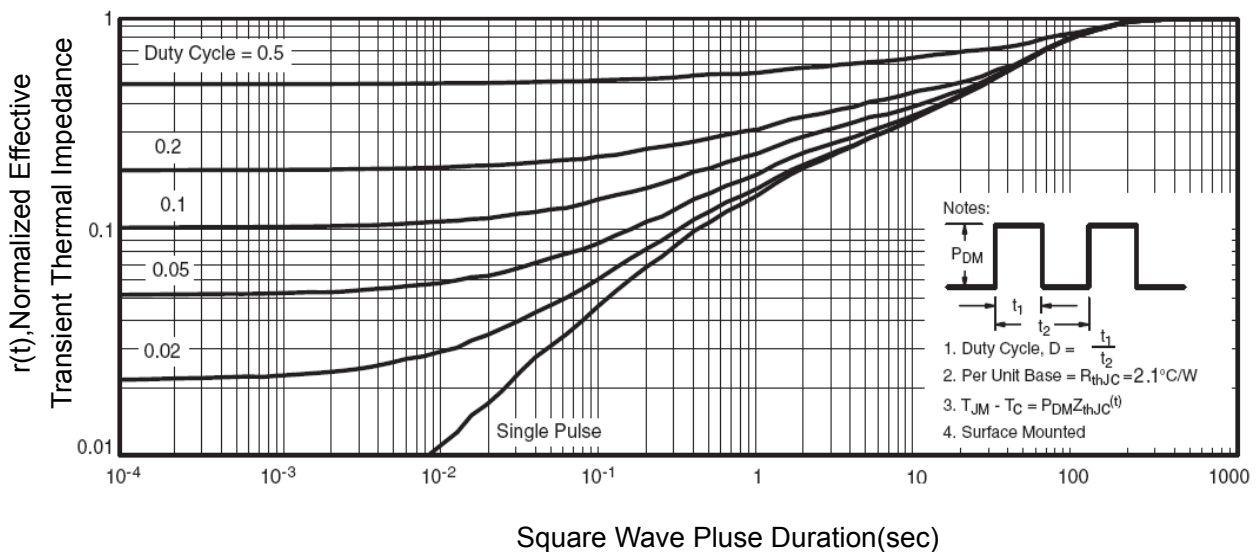
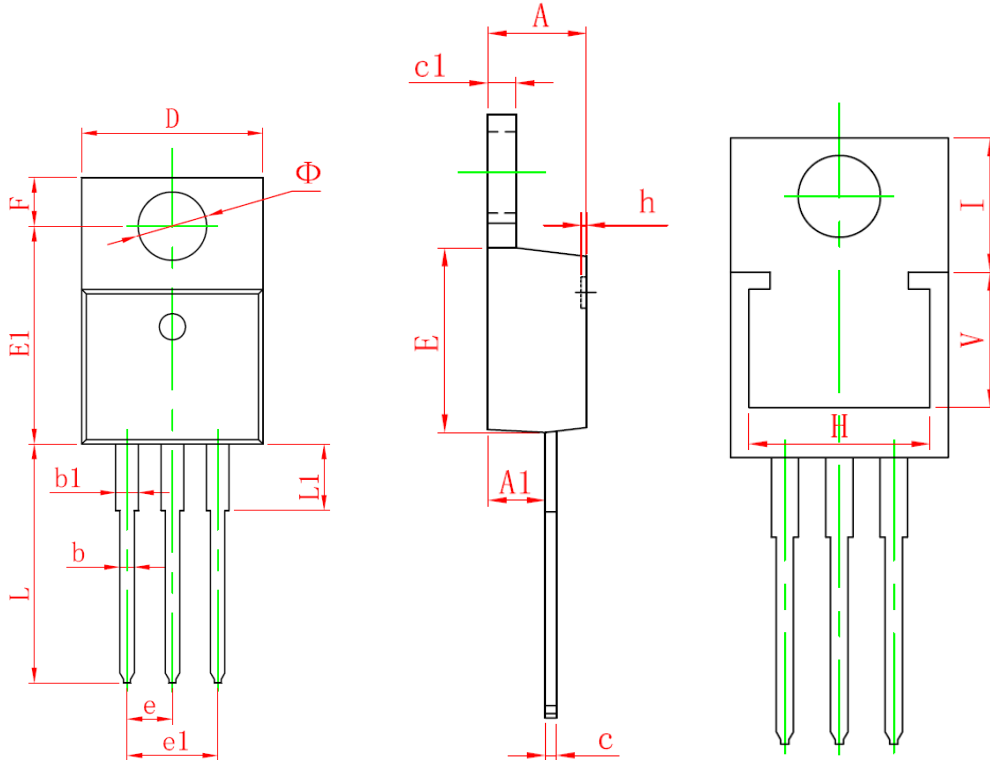


Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	10.010	10.350	0.394	0.407
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 (TYP.)		0.100 (TYP.)	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
H	8.440 REF.		0.332 REF.	
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
V	6.360 REF.		0.250 REF.	
I	6.300 REF.		0.248 REF.	
Φ	3.735	3.935	0.147	0.155